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U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Substitute for form 1448A/PTO				Complete If Known	
				Application Number	09/943,199
				Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell
				Art Unit	2818
				Examiner Name	D. Vu
Sheet	1	of	5	Attorney Docket Number	M4065.0704/P704

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
D✓	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AD	2002/0123189	09/05/2002	Moore et al.	
	AE	2002/0123170	09/05/2002	Moore et al.	
	AF	2002/0123248	09/05/2002	Moore et al.	
	AG	2002/0127888	09/12/2002	Moore et al.	
	AH	2002/0132417	09/09/2002	Li	
	AI	2002/0160551	10/31/2002	Harshfield	
	AJ	2002/0163828	11/07/2002	Krieger et al.	
	AK	2002/0168820	11/2002	Kozicki	
	AL	2002/0168852	11/2002	Kozicki	
	AM	2002/0190289	12/19/2002	Harshfield et al.	
	AN	2002/0180350	12/19/2002	Kozicki et al.	
	AO	2003/0001229	01/02/2003	Moore et al.	
	AP	2003/0027416	02/06/2003	Moore	
	AQ	2003/0032254	02/13/2003	Gilton	
	AR	2003/0035314	02/20/2003	Kozicki	
	AS	2003/0035315	02/20/2003	Kozicki	
	AT	2003/0038301	02/27/2003	Moore	
D✓	AU	2003/0043631	03/06/2003	Gilton et al.	
	AV	2003/0045049	3/2003	Campbell et al.	
D✓	AW	2003/0045054	3/2003	Campbell et al.	
	AX	2003/0047765	03/13/2003	Campbell	
	AY	2003/0047772	03/13/2003	Li	
	AZ	2003/0047773	03/13/2003	Li	
	AA1	2003/0048519	03/13/2003	Kozicki	
	AB1	2003/0048744	3/2003	Ovshinsky et al.	
	AC1	2003/0049912	03/13/2003	Campbell et al.	
	AD1	2003/0068861	4/2003	Li et al.	
	AE1	2003/0068862	4/2003	Li et al.	
	AF1	2003/0095428	05/22/2003	Hush et al.	
	AG1	2003/0098497	5/2003	Moore et al.	
	AH1	2003/0107105	6/2003	Kozicki	
	AI1	2003/0117831	06/26/2003	Hush	
	AJ1	2003/0128612	07/10/2003	Moore et al.	
	AK1	2003/0137869	07/24/2003	Kozicki	
	AL1	2003/0143782	07/31/2003	Gilton et al.	
	AM1	2003/0155589	08/21/2003	Campbell et al.	
	AN1	2003/0155608	08/21/2003	Campbell et al.	
	AO1	2003/0156447	08/21/2003	Kozicki	
D✓	AP1	2003/0156463	08/21/2003	Casper et al.	
D✓	AQ1	2003/0209728	11/13/2003	Kozicki et al.	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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P✓	AR1	2003/0209971	11/13/2003	Kozicki et al.	
	AS1	2003/0210584	11/13/2003	Kozicki et al.	
	AT1	2003/0212724	11/2003	Ovshinsky et al.	
	AU1	2003/0212725	11/2003	Ovshinsky et al.	
	AV1	2004/0035401	2/2004	Ramachandran et al.	
	AW1	RE 37,259E	7/2001	Ovshinsky	
	AX1	3,271,591	9/1968	Ovshinsky	
	AY1	3,861,314	6/1976	Klose et al.	
	AZ1	3,866,317	6/1976	Wacks et al.	
	AA2	3,983,542	11/1976	Ovshinsky	
	AB2	3,988,720	10/1976	Ovshinsky	
	AC2	4,177,474	12/1979	Ovshinsky	
	AD2	4,267,281	5/1981	Hallman et al.	
	AE2	4,316,948	1/1982	Masters, et al.	
	AF2	4,597,162	7/1986	Johnson et al.	
	AG2	4,608,298	8/1986	Keem et al.	
	AH2	4,637,895	1/1987	Ovshinsky et al.	
	AJ2	4,646,266	2/1987	Ovshinsky et al.	
	AJ2	4,664,939	5/1987	Ovshinsky	
	AK2	4,668,968	5/1987	Ovshinsky et al.	
	AL2	4,670,763	6/1987	Ovshinsky et al.	
	AM2	4,671,618	6/09/1987	Wu et al.	
	AN2	4,673,957	6/1987	Ovshinsky et al.	
	AO2	4,678,679	7/1987	Ovshinsky	
	AP2	4,698,758	9/1987	Ovshinsky et al.	
	AQ2	4,698,234	10/1987	Ovshinsky et al.	
	AR2	4,710,899	12/1987	Young et al.	
	AS2	4,728,406	3/1988	Banerjee et al.	
	AT2	4,737,379	4/1988	Hudgens et al.	
	AU2	4,766,471	8/1988	Ovshinsky et al.	
	AV2	4,769,338	9/1988	Ovshinsky et al.	
	AW2	4,775,425	10/1988	Guha et al.	
	AX2	4,788,594	11/1988	Ovshinsky et al.	
	AY2	4,800,526	01/24/1989	Lewis	
	AZ2	4,809,044	2/1989	Pryor et al.	
	AA3	4,818,717	4/1989	Johnson et al.	
	AB3	4,843,443	6/1989	Ovshinsky et al.	
	AC3	4,845,533	7/1989	Pryor et al.	
	AD3	4,853,785	8/1989	Ovshinsky et al.	
	AE3	4,891,330	1/1990	Guha et al.	
	AF3	5,128,099	7/1992	Strand et al.	
	AG3	5,159,661	10/1992	Ovshinsky et al.	
	AH3	5,166,758	11/1992	Ovshinsky et al.	
	AI3	5,272,359	12/21/1993	Nagasubramanian et al.	
	AJ3	5,298,718	3/1994	Ovshinsky et al.	
	AK3	5,314,772	5/24/1994	Kozicki	
	AL3	5,335,219	8/1994	Ovshinsky et al.	
✓	AM3	5,341,328	8/1994	Ovshinsky et al.	
D✓	AN3	5,359,205	10/1994	Ovshinsky	

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				Complete if Known
Sheet	3	of	5	
				Attorney Docket Number M4065.0704/P704

P✓	AO3 5,406,509	4/1995	Ovshinsky et al.	
	AP3 5,414,271	5/1995	Ovshinsky et al.	
	AQ3 5,534,711	7/1996	Ovshinsky et al.	
	AR3 5,534,712	7/1996	Ovshinsky et al.	
	AS3 5,536,947	7/1996	Klersy et al.	
	AT3 5,543,737	8/1996	Ovshinsky	
	AU3 5,591,501	1/1997	Ovshinsky et al.	
	AV3 5,596,522	1/1997	Ovshinsky et al.	
	AW3 5,687,112	11/1997	Ovshinsky	
	AX3 5,694,054	12/1997	Ovshinsky et al.	
	AY3 5,714,768	2/1998	Ovshinsky et al.	
	AZ3 5,814,527	9/29/1998	Walstenholme et al.	
	AA4 5,818,749	10/06/1998	Harshfield	
	AB4 5,826,046	10/1998	Czubatyj et al.	
	AC4 5,851,882	12/22/1998	Harshfield	
	AD4 5,869,843	2/9/1999	Harshfield	
	AE4 5,912,839	6/1999	Ovshinsky et al.	
	AF4 5,933,365	8/1999	Klersy et al.	
	AG4 6,011,757	1/2000	Ovshinsky	
	AH4 6,031,287	2/29/2000	Harshfield	
	AI4 6,072,716	06/06/2000	Jacobson et al.	
	AJ4 6,087,674	7/2000	Ovshinsky et al.	
	AK4 6,141,241	10/2000	Ovshinsky et al.	
	AL4 6,339,544	1/2002	Chiang et al.	
	AM4 6,404,665	6/2002	Lowery et al.	
	AN4 6,428,064	8/2002	Wicker	
	AO4 6,437,383	8/2002	Xu	
	AP4 6,440,837	8/27/2002	Harshfield	
	AQ4 6,452,984	10/2002	Xu et al.	
	AR4 6,473,332	10/2002	Ignatiev et al.	
	AS4 6,480,438	11/2002	Park	
	AT4 6,487,106	11/26/2002	Kozicki	
	AU4 6,487,113	11/2002	Park et al.	
	AV4 6,501,111	12/2002	Lowery	
	AW4 6,507,061	1/2003	Hudgens et al.	
	AX4 6,511,862	1/2003	Hudgens et al.	
	AY4 6,511,867	1/2003	Lowery et al.	
	AZ4 6,512,241	1/2003	Lai	
	AA5 6,514,805	2/2003	Xu et al.	
	AB5 6,531,373	3/2003	Gill et al.	
	AC5 6,534,781	3/2003	Dennison	
	AD5 6,545,287	4/2003	Chiang	
	AE5 6,545,907	4/2003	Lowery et al.	
	AF5 6,555,860	4/2003	Lowery et al.	
	AG5 6,583,184	5/2003	Lowery et al.	
	AH5 6,566,700	5/2003	Xu	
	AI5 6,567,293	5/2003	Lowery et al.	
✓	AJ5 6,569,705	5/2003	Chiang et al.	
✓	AK5 6,570,784	5/2003	Lowery	

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		First Named Inventor	Kristy A. Campbell
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D✓	AL5	6,576,921	6/2003	Lowery	
	AM5	6,586,761	7/2003	Lowery	
	AN5	6,589,714	7/2003	Maimon et al.	
	AOS	6,590,807	7/2003	Lowery	
	AP5	6,593,178	7/2003	Dennison	
	AQ5	6,597,009	7/2003	Wicker	
	AR5	6,605,527	8/2003	Dennison et al.	
	AS5	6,613,604	9/2003	Maimon et al.	
	AT5	6,621,095	9/2003	Chiang et al.	
	AU5	6,625,054	9/2003	Lowery et al.	
	AV5	6,642,102	11/2003	Xu	
	AW5	6,646,297	11/2003	Dennison	
	AX5	6,649,928	11/2003	Dennison	
	AY5	6,667,900	12/2003	Lowery et al.	
	AZ5	6,671,710	12/2003	Ovshinsky et al.	
	AA6	6,673,648	1/2004	Lowrey	
	AB6	6,673,700	1/2004	Dennison et al.	
	AC6	6,674,115	1/2004	Hudgens et al.	
	AD6	6,687,153	2/2004	Lowery	
	AE6	6,687,427	2/2004	Ramalingam et al.	
	AF6	6,690,026	2/2004	Peterson	
	AG6	6,696,355	2/2004	Dennison	
	AH6	6,707,712	3/2004	Lowery	
D✓	AI6	6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.*	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code* -Number* -Kind Code* (if known)			
BA	56126916		10/19981	Akira et al.	
BB	WO 97/08032		12/18/1997	Kozicki et al.	
BC	WO 89/28914		09/16/1989	Kozicki et al.	
BD	WO 00/48186		08/17/2000	Kozicki et al.	
BE	WO 02/21542		03/14/2002	Kozicki et al.	

Examiner Signature	<i>Shulman</i>	Date Considered	12/08/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*Applicant's unique citation designation number (optional). *See attached Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. *Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). *For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. *Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. *Applicant is to place a check mark here if English language Translation is attached.

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Group Art Unit	2818
Examiner Name	D. Vu

Attorney Docket Number M4065.0704/P704

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DV	CA	Kawamoto, Y., Nishida, M., Ionic Condition in As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses, J. Non-Cryst Solids 20(1976) 393-404.	
	CB	Kozicki et al., Silver incorporation in thin films of selenium rich Ge-Se glasses, International Congress on Glass, Volume 2, Extended Abstracts, July 2001, pgs. 8-9.	
	CC	Michael N. Kozicki, 1. Programmable Metallization Cell Technology Description, February 18, 2000	
	CD	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000	
	CE	Kozicki et al., Applications of Programmable Resistance Changes In Metal-Doped Chalcogenides, Electrochemical Society Proceedings, Volume 99-13, 1999, pgs. 298-309.	
	CF	Kozicki et al., Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures, Vol. 27, No. 516, 2000, pgs. 485-488.	
	CG	Kozicki et al., Nanoscale phase separation in Ag-Ge-Se glasses, Microelectronic Engineering 63 (2002) pgs 155-159.	
✓	CH	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.	
DV	CI	Miyatani, S.-y., Electrical properties of Ag ₂ Se, J. Phys. Soc. Japan 13 (1958) 317.	

Examiner Signature	<i>Shuland</i>	Date Considered	12/08/04
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¹EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Application Number	09/943,199			
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	First Named Inventor	Kristy A. Campbell, et al.			
	Art Unit	2818			
Examiner Name	David Vu				
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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

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		Country Code ² -Number ³ -Kind Code ⁴ (# known)				
DV	BA	WO 97/488032	12/18/1997	Kozicki et al.		
DV	BB	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	Shulard	Date Considered	12/08/04
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 801.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3.) ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Examiner Name				
				Attorney Docket Number

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
DV	CA	Abdel-Ali, A.; Elshafie,A.; Elshawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.		T ²
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.		
	CE	Afifi,M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state ionics 136-137 (2000) 1085-1089.		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
	CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state ionics 136-137 (2000) 1025-1029.		
	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag ₇ GeSe ₅ I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.		
	CO	Bennmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4.		
	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
	CR	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.		
	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
	CT	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.		
	CU	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.		
↓	CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg ₄ I ₅ , Solid State Ionics 70/71 (1994) 72-76.		
DV	CW	Boothchand, P., The maximum in glass transition temperature (T _g) near x=1/3 in GexSe1-x		

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Sheet	3	of	8	Attorney Docket Number
D✓				2000-12-12 14:41:11 PM

		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
D✓	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes. Nature 410 (2001) 1070-1073.	
	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CC1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe1-x glasses, Solid state comm. 45 (1983) 183-185.	
	CD1	Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (Tg), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
	CE1	Boolchand, P.; Grothaus, J. Molecular Structure of Melt-Quenched GeSe2 and GeS2 glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.	
	CF1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CG1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe2 glass, Hyperfine Interactions 27 (1986) 389-392.	
	CI1	Cahen, D.; Gillet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe2 Crystals, Science 258 (1992) 271-274.	
	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Teinic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
	CR1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
D✓	CU1	Drusdau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous	

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Group Art Unit

Examiner Name

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Attorney Docket Number

DV	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
CV1	El Bouchairi, B.; Bemedje, J.C.; Burgaud, P., Properties of Ag _{2-x} Se _{1+x} /n-Si diodes, Thin Solid Films 110 (1983) 107-113.
CW1	El Gharris, Z.; Bourahla, A.; Vaulier, C., Role of photinduced defects in amorphous Ge _x Se _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.
CX1	El Ghundi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.
CY1	El Ghundi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe5.5 thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.
CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.
CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.
CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.
CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.
CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.
CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.
CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se ₇₅ Ge ₇ Sb ₁₈ , Vacuum 43 (1992) 253-257.
CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.
CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.
CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe ₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.
CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vaulier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.
CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.
CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.
CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag ₂ Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.
CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.
CO2	Guin, J.-P.; Rouxel, T.; Kervyn, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.
CP2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.
DV	CQ2 Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.

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				Application Number
				Filing Date
				First Named Inventor
				Group Art Unit
				Examiner Name
Sheet	5	of	8	Attorney Docket Number
D✓	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.		
	CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954.		
	CT2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.		
	CU2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.		
	CV2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.		
	CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.		
	CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.		
	CY2	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.		
	CA3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V ₂ amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.		
	CB3	Hosokawa, S., Atomic and electronic structures of glassy Ge _x Se _{1-x} around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.		
	CC3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.		
	CD3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B 74 (1996) 37-50.		
	CE3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.		
	CF3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.		
	CG3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge ₂ S ₃ , J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.		
	CH3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.		
	CI3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.		
	CJ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As ₂ Se ₇ before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.		
	CK3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As ₂ Se ₅ , Mat. Res. Bull. 8 (1973) 433-442.		
	CL3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.		
	CM3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1998) 9098-9104.		
↓	CN3	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Jpn. J. Appl. Phys. 26 (1987) 15-21.		
D✓	CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Ag _x (GeSe ₃) _{1-x} (0<=x<=0.571) glasses, Solid state ionics 123 (1999) 259-269.		

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Complete If Known

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GROUP 3600

DV	CP3	Kluge, G.; Thomas, A.; Klubes, R.; Grotzschel, R., Silver photodiffusion in amorphous Ge _x Se _{100-x} . J. Non-Cryst. Solids 124 (1990) 186-193.
	CQ3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides. J. Non-Cryst. Solids 198-200 (1996) 728-731.
	CR3	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films. J. Non-Cryst. Solids 137-138 (1991) 1027-1030.
	CS3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts. J. Non-Cryst. Solids 194 (1996) 256-259.
	CT3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSETI chalcogenide semiconductor films. Thin Solid Films 240 (1994) 143-146.
	CU3	Lakshminarayana, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism. J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.
	CV3	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses. Indian Journal of pure & appl. phys. 29 (1991) 303-304.
	CW3	Lelmer, F.; Stotzel, H.; Kotwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction. Phys. Stat. Sol. (a) 29 (1975) K129-K132.
	CX3	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in Ge _x Se _{1-x} glass. Appl. Phys. Lett. 46 (1985) 543-545.
	CY3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO ₂ system. Jap. J. Appl. Phys. 11 (1972) 1657-1662.
	CZ3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films. Jpn. J. Appl. Phys. 11 (1972) 606.
	CA4	Mazunier, F.; Levy, M.; Souquet, J.L., Reversible and irreversible electrical switching in TeO ₂ -V ₂ O ₅ based glasses. Journal de Physique IV 2 (1992) C2-185 - C2-188.
	CB4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni,Bi). Mat. Chem. And Phys. 28 (1991) 253-258.
	CC4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory. J. Non-Cryst. Solids 240 (1998) 1-21.
→	CD4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices. J. Non-Cryst. Solids 299-302 (2002) 1023-1027.
	CF4	Miyatani, S.-y., Electronic and ionic conduction in (Ag _x Cu _{1-x}) ₂ Se. J. Phys. Soc. Japan 34 (1973) 423-432.
	CH4	Miyatani, S.-y., Ionic conduction in beta-Ag ₂ Te and beta-Ag ₂ Se. Journal Phys. Soc. Japan 14 (1959) 998-1002.
	CI4	Mott, N.F., Conduction in glasses containing transition metal ions. J. Non-Cryst. Solids 1 (1968) 1-17.
	CJ4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films. Jpn. J. Appl. Phys. 32 (1993) 564-569.
	CK4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses. Jpn. J. Appl. Phys. 39 (2000) 6157-6161.
	CL4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of Ge _x Se _{1-x} amorphous thin films. Jap. J. App. Phys. 15 (1976) 849-853.
	CM4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses. Phys. Rev. B 54 (1996) 4413-4415.
↓	CN4	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories. IEEE transactions on electron dev. Ed-20 (1973) 195-209.
DV	CO4	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic. Metallurgical transactions 2 (1971) 641-645.

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	Group Art Unit	1211	
	Examiner Name	JET	
Sheet	7	of	8
			Attorney Docket Number

D✓	CP4	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.	
	CQ4	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54	
	CR4	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.	
	CS4	Owen, A.E.; Le Comber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.	
	CT4	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.	
	CU4	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.	
	CV4	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.	
	CW4	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.	
	CX4	Popov, A.I.; Geller, I.Kh.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.	
	CY4	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.	
	CZ4	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ga-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.	
	CA5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.	
	CB5	Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.	
	CC5	Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.	
	CD5	Schuocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J. Non-Cryst. Solids 29 (1978) 397-407.	
	CES	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.	
	CF5	Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.	
	CG5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
	CH5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, I.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.	
	CI5	Steventon, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.	
	CJ5	Steventon, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.	
	CK5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.	
	CL5	Tanaka, K., Ionic and mixed conduction in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.	
D✓	CM5	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.	

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449B/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet			8	of	8	Complete if Known
						Attorney Docket Number

DV	CNS	Thomburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.				
	CO5	Thomburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 3 (1972) 113-120.				
	CP5	Thomburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612.				
	CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in Ge _x Se _{1-x} and As _x Se _{1-x} systems, J. Non-Cryst. Solids 261 (2000) 277-281.				
	CR5	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.				
	CS5	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, 9-13 September 1985.				
	CT5	Tregouet, Y.; Bermede, J.C., Silver movements in Ag ₂ Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.				
	CUS	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge _{0.4} Se _{0.6} , J. Non-Cryst. Solids 117-118 (1990) 219-221.				
	CV5	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.				
	CD5	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1978) 267-272.				
	CX5	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454.				
	CY5	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.				
	CZ5	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.				
DV	CC6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T _g , with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope dT _g /d<m> at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.				

Examiner Signature	<i>Shubra</i>	Date Considered	12/08/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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